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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/659,728	09/10/2003	Yongjun Jeff Hu	MICRON.165DV1	3883
20995	7590 07/30/2004		EXAMINER	
KNOBBE M	ARTENS OLSON & BEA	NHU, DAVID		
2040 MAIN S FOURTEENT			ART UNIT	PAPER NUMBER
IRVINE, CA			2818	
			DATE MAILED: 07/30/2004	4

Please find below and/or attached an Office communication concerning this application or proceeding.

		Application No.	Applicant(s)			
Office Action Summary		10/659,728	HU, YONGJUN JEFF			
		Examiner	Art Unit			
		David Nhu	2818			
Period f	The MAILING DATE of this communication a or Reply	ppears on the cover sheet w	vith the correspondence addres	is		
THE - External control	MAILING DATE OF THIS COMMUNICATION MAILING DATE OF THIS COMMUNICATION ensions of time may be available under the provisions of 37 CFR or SIX (6) MONTHS from the mailing date of this communication. The period for reply specified above is less than thirty (30) days, a report of the period for reply is specified above, the maximum statutory period to reply within the set or extended period for reply will, by static reply received by the Office later than three months after the mained patent term adjustment. See 37 CFR 1.704(b).	I.  1.136(a). In no event, however, may a eply within the statutory minimum of th d will apply and will expire SIX (6) MC ute, cause the application to become	a reply be timely filed irty (30) days will be considered timely. INTHS from the mailing date of this commu ABANDONED (35 U.S.C. § 133).	nication.		
Status						
1)⊠	Responsive to communication(s) filed on 10	September 2003.				
2a) <u></u>		nis action is non-final.				
3)[						
	closed in accordance with the practice under Ex parte Quayle, 1935 C.D. 11, 453 O.G. 213.					
Disposit	ion of Claims					
4)⊠	Claim(s) 1-8 is/are pending in the application	١.				
	4a) Of the above claim(s) is/are withd	rawn from consideration.				
5)□	Claim(s) is/are allowed.					
6)⊠	Claim(s) <u>1-8</u> is/are rejected.					
7)	Claim(s) is/are objected to.					
8)□	Claim(s) are subject to restriction and	/or election requirement.				
Applicat	tion Papers					
9) 🗌	The specification is objected to by the Exami	ner.				
10)	The drawing(s) filed on is/are: a) a	ccepted or b) Objected to	by the Examiner.			
	Applicant may not request that any objection to the	ne drawing(s) be held in abey	ance. See 37 CFR 1.85(a).			
	Replacement drawing sheet(s) including the corre					
11)	The oath or declaration is objected to by the	Examiner. Note the attach	ed Office Action or form PTO-1	· <b>52</b> .		
-	under 35 U.S.C. § 119					
	Acknowledgment is made of a claim for foreign All b) Some * c) None of:  1. Certified copies of the priority docume  2. Certified copies of the priority docume  3. Copies of the certified copies of the priority docume	ents have been received. ents have been received in riority documents have bee	Application No. <u>09/887,449</u> .	ge		
*	See the attached detailed Office action for a li	•	ot received.			
	COO MIC AMAGINES ACIANICA CINICO ACIANI IOI A II					
Attachmei	nt(s)	X	and of the			
1) 🛛 Noti	ce of References Cited (PTO-892)		Summary (PTO-413)			
2) Noti	ce of Draftsperson's Patent Drawing Review (PTO-948)	Paper N	o(s)/Mail Date f Informal Patent Application (PTO-152	2)		
	rmation Disclosure Statement(s) (PTO-1449 or PTO/SB/0 er No(s)/Mail Date <u>01</u> .	6) Other: _	***	-/		

#### **DETAIL ACTIONS**

## **Drawings**

1. There is no description of (134) in figure 4. Also, there is no description of **the layer** on the layer 124 in the figure 4.

## Claim Rejections - 35 USC § 112

- 2. The following is a quotation of the second paragraph of 35 U.S.C. 112:
  - The specification shall conclude with one or more claims particularly pointing out and distinctly claiming the subject matter which the applicant regards as his invention.
- 3. Claims 1-2 are rejected under 35 U.S.C. 112, second paragraph, as being indefinite for failing to particularly point out and distinctly claim the subject matter which applicant regards as the invention.
- Claim 1, " the work function " lacks a clear antecedent basis.
- Claim 2, "the adjacent layers " lacks a clear antecedent basis.

# Claim Rejections - 35 USC 103

- 4. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this office action:
  - (a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.
- 5. Claims 1-8 are rejected under 35 U.S.C. 103(a) as being unpatentable over Background of Invention (BOI) in view of Gardner et al (5,854,115).

**Regarding claims 1,** (see BOI, figure 1, pages 1-4), teach a semiconductor device comprising: a semiconductor substrate (PMOS,NMOS); a dielectric layer (SiOH) positioned on the semiconductor substrate; an interconnecting layer (TiNx).

It is noted that BOI fails to teach a metal silicide wherein the metal is matched with the silicide so that the metal is inhibited from reacting with the dielectric layer and also wherein the metal is selected such that selective nitrification of the metal silicide lowers the work function of the metal silicide.

However, Gardner, (see figures 8-12, col. 6, lines 24-67, col. 7, lines 1-19), teach a metal silicide 68 wherein the metal is matched with the silicide so that the metal is inhibited from reacting with the dielectric layer 52 and also wherein the metal is selected such that selective nitrification of the metal silicide lowers the work function of the metal silicide.

Regarding claims 2-8, BOI, pages 1-4, and Gardner, col. 1-8, also teach the metal selected is the metal silicide; the conductive layer on the interconnecting layer such that the dielectric layer together define a gate stack; wherein the metal comprises tantalum; the substrate is silicon and the dielectric layer is silicon oxide; the conductive layer comprises tungsten, cobalt, nickel, silicide.

It would have been obvious to one having ordinary skill in the art at the time of the present invention to apply the teachings of Gardner into the method of BOI as both are related to the same subject matter of fabricating a semiconductor device having a gate stack, a gate oxide, isolation structures, a conductive layer, a metal silicide interconnecting layer for contacting the conductive layer, the metal is selected selective nitrification of the metal silicide.

#### Conclusion

6. The prior art made of record and not relied upon is considered pertinent to

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applicant's disclosure: Tseng'557 is cited as of interest.

7. A shortened statutory period for response to this action is set to expired 3 (three) months

and 0 (zero) day from the date of this letter. Failure to respond within the period for response

will cause the application to become abandoned (see 710.02 (b)).

8. Any inquiry concerning this communication on earlier communications from the examiner

should be directed to David Nhu, (571)272-1792. The examiner can normally be reached on

Monday-Friday from 7:30 AM to 5:00 PM. The examiner's supervisor, David Nelms can be

reached on (571)272-1787.

The fax phone number for the organization where this application or proceeding is assigned is

(703)872-9306.

Any inquiry of a general nature or relating to the status of this application or proceeding should

be directed to the receptionist whose telephone number is (703) 308-0956

David Nhu

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July 27, 2004

Dui Dan